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## N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>(BR)DSS</sub> (V)	$r_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>a</sup>		
20	0.0046 at V <sub>GS</sub> = 4.5 V	65		
	0.0062 at V <sub>GS</sub> = 2.5 V	40		

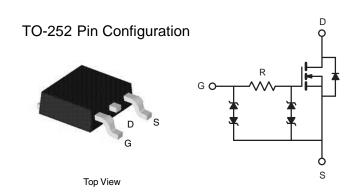
### **FEATURES**

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- 100 % R<sub>g</sub> Tested
- 100 % UIS Tested
- Typical ESD Protection 4000 V



### **APPLICATIONS**

OR-ing



Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	20	V	
Gate-Source Voltage	V <sub>GS</sub>	± 12	V		
Continuous Drain Current (T <sub>.1</sub> = 175 °C)	T <sub>C</sub> = 25 °C	I-	65 <sup>a</sup>		
Continuous Diam Current (1j = 175 C)	T <sub>C</sub> = 100 °C	I <sub>D</sub>	45 <sup>a</sup>	А	
Pulsed Drain Current		I <sub>DM</sub>	210		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	50		
Single Pulse Avalanche Energy	_ L=0.11IIII	E <sub>AS</sub>	125	mJ	
Mariana Barra Biasinatia d	T <sub>C</sub> = 25 °C	D D	120 <sup>c</sup>	14/	
Maximum Power Dissipation <sup>b</sup>	T <sub>A</sub> = 25 °C <sup>d</sup>	P <sub>D</sub>	3.75	W	
Operating Junction and Storage Temperature Ra	nge	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) <sup>d</sup>	R <sub>thJA</sub>	40	°C/W		
Junction-to-Case	R <sub>thJC</sub>	1.25	1 10/00		

#### Notes:

- a. Package limited.

- b. Duty cycle ≤ 1 %.
  c. See SOA curve for voltage derating.
  d. When mounted on 1" square PCB (FR-4 material).



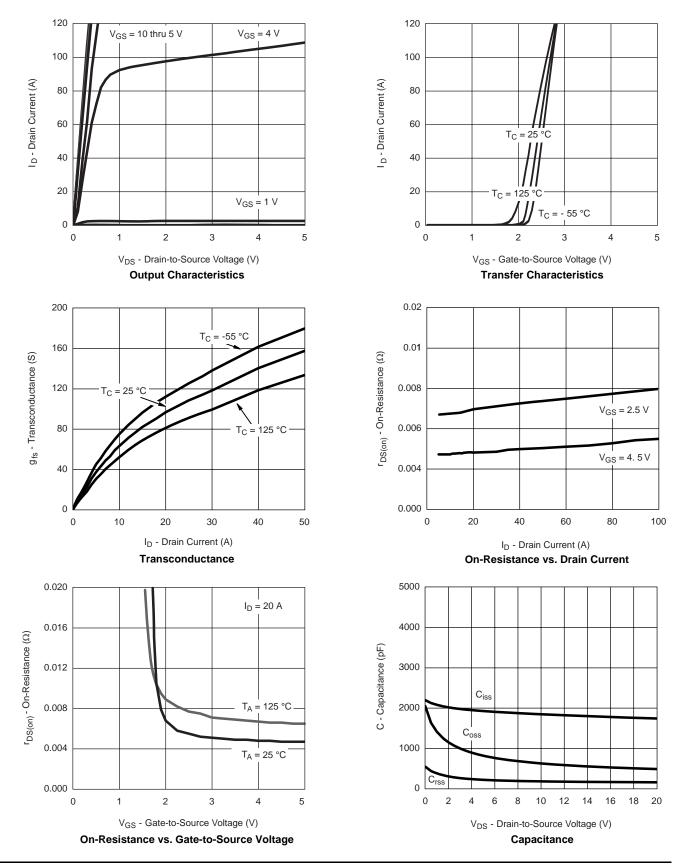
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static					<u>l</u>		
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	20			١/	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.5		1.2	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 10	uA	
	I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$			1 50 μ/		
Zero Gate Voltage Drain Current		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C					
		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250	1	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	100			Α	
		$V_{GS} = 4.5 \text{ V}, I_D = 5 \text{ A}$		0.0046	0.0060	†	
	_	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}, T_J = 125 \text{ °C}$			0.007		
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C			0.008	Ω	
		$V_{GS} = 2.5 \text{ V}, I_D = 10 \text{ A}$		0.0062	0.0083		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 10 A		95		S	
Dynamic <sup>b</sup>					<u> </u>		
Input Capacitance	C <sub>iss</sub>			2050		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 10 \text{ V}, f = 1 \text{ MHz}$		485			
Reverse Transfer Capacitance	C <sub>rss</sub>			205			
Total Gate Charge <sup>b</sup>	$Q_g$			27	50		
Gate-Source Charge <sup>b</sup>	$Q_{gs}$	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 50 \text{ A}$		6.5		nC	
Gate-Drain Charge <sup>b</sup>	$Q_{gd}$			7			
Gate Resistance	$R_{g}$		0.75	1.5	2.3	Ω	
Turn-On Delay Time <sup>b</sup>	t <sub>d(on)</sub>			15	25		
Rise Time <sup>b</sup>	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 0.2 $\Omega$		7	11		
Turn-Off Delay Time <sup>b</sup>	t <sub>d(off)</sub>	$I_D \cong 50 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1.0$		35	55	ns	
Fall Time <sup>b</sup>	t <sub>f</sub>	Ω		8	12		
Source-Drain Diode Ratings and Cha	racteristics T	<sub>C</sub> = 25 °C <sup>c</sup>		•			
Continuous Current	I <sub>S</sub>				65	۸	
Pulsed Current	I <sub>SM</sub>				210	Α	
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = 20 \text{ A}, V_{GS} = 0 \text{ V}$		0.85	1.2	V	
Reverse Recovery Time	t <sub>rr</sub>			25	55	ns	
Peak Reverse Recovery Current	I <sub>RM</sub>	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		1.7	3.4	Α	
Reverse Recovery Charge	Q <sub>rr</sub>			0.024	0.105	μC	

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Independent of operating temperature.
- c. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

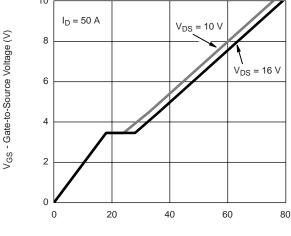


## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

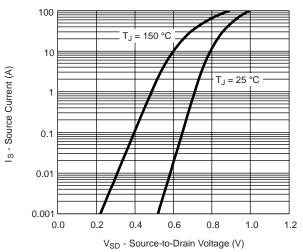


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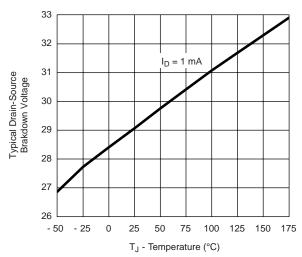
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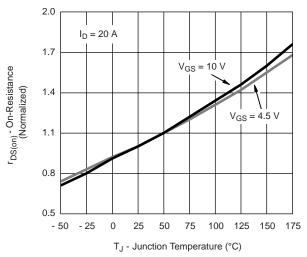
 $\mathbf{Q}_{g}$  - Total Gate Charge (nC)  $\mathbf{Gate\ Charge}$ 



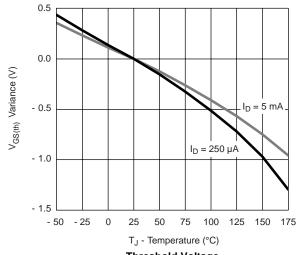
Source-Drain Diode Forward Voltage



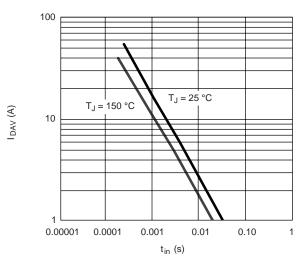
Typical Drain-Source Brakdown Voltage vs. Junction Temperature



On-Resistance vs. Junction Temperature



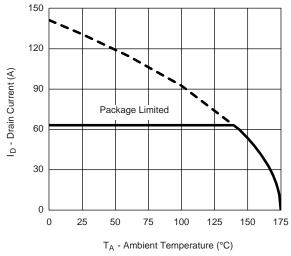
Threshold Voltage

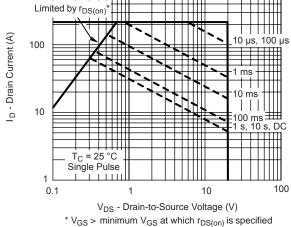


Single Pulse Avalanche Current vs. Time

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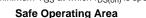
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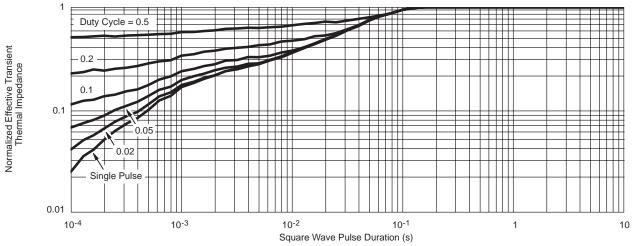




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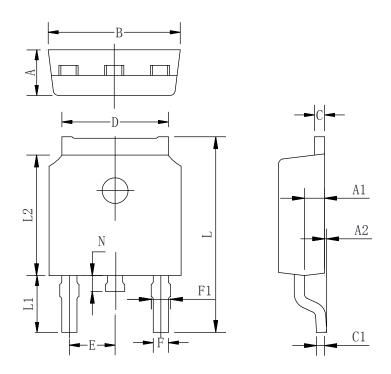
**Drain Current vs. Ambient Temperature** 





Normalized Thermal Transient Impedance, Junction-to-Case

# TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max
A	2.10	2.30	2.50
A1	0.88	1.01	1.16
A2	0.00	0.15	0.28
В	6.40	6.60	6.80
C	0.42	0.50	0.63
C1	0.42	0.50	0.63
D	5.08	5.32	5.65
Е	2.286 TYP		
F	0.63	0.76	0.89
F1	0.64	0.86	1.08
L	9.30	9.90	10.80
L1	2.4	2.8	3.6
L2	5.90	6.10	6.55
N	0.57	0.80	1.05





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